

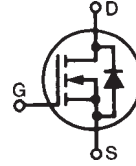
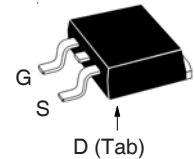
TrenchT4™
Power MOSFET
IXTA340N04T4
IXTA340N04T4-7

$$V_{DSS} = 40V$$

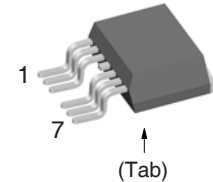
$$I_{D25} = 340A$$

$$R_{DS(on)} \leq 1.7m\Omega$$

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Rectifier


TO-263 AA


G = Gate D = Drain
 S = Source Tab = Drain

TO-263 (7-Leads)


Pins: 1 - Gate
 2, 3, 5, 6, 7 - Source
 4 (Tab) - Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $175^\circ C$	40	V
V_{DGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GS} = 1M\Omega$	40	V
V_{GSM}	Transient	± 15	V
I_{D25}	$T_C = 25^\circ C$	340	A
I_{LRMS}	Lead Current Limit, RMS	160	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	750	A
I_A	$T_C = 25^\circ C$	170	A
E_{AS}	$T_C = 25^\circ C$	1.2	J
I_A	$T_C = 25^\circ C$	340	A
E_{AS}	$T_C = 25^\circ C$	500	mJ
P_D	$T_C = 25^\circ C$	480	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
F_C	Mounting Force	10..65 / 2.2..14.6	N/lb
Weight	TO-263	2.5	g
	TO-263 (7Leads)	3.0	g

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	40		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 15V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ C$			5 μA
				750 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 100A$, Notes 1, 2			1.7 m Ω

Features

- International Standard Packages
- $175^\circ C$ Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converters & Off-Line UPS
- Primary-Side Switch
- High Current Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	115	195	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		13	nF
C_{oss}			1850	pF
C_{rss}			1226	pF
R_{Gi}	Gate Input Resistance		1.1	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External)		23	ns
t_r			55	ns
$t_{d(off)}$			113	ns
t_f			40	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		256	nC
Q_{gs}			64	nC
Q_{gd}			86	nC
R_{thJC}				0.31 $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			340 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			1360 A
V_{SD}	$I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 150\text{A}$, $V_{GS} = 0\text{V}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 30\text{V}$		43	ns
I_{RM}			10	A
Q_{RM}			210	nC

- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
 2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

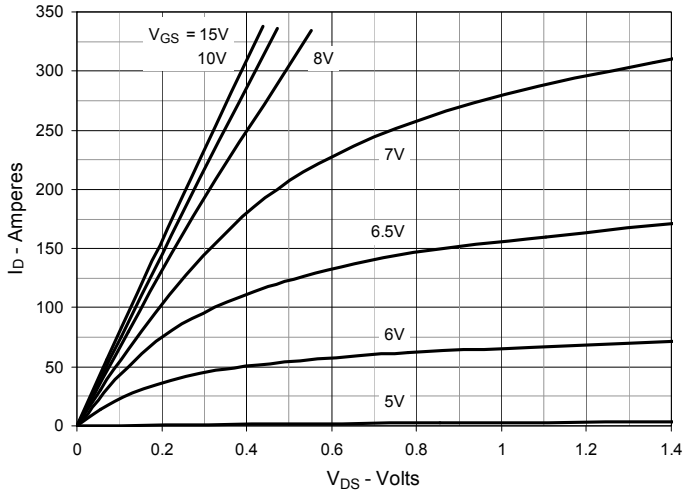


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

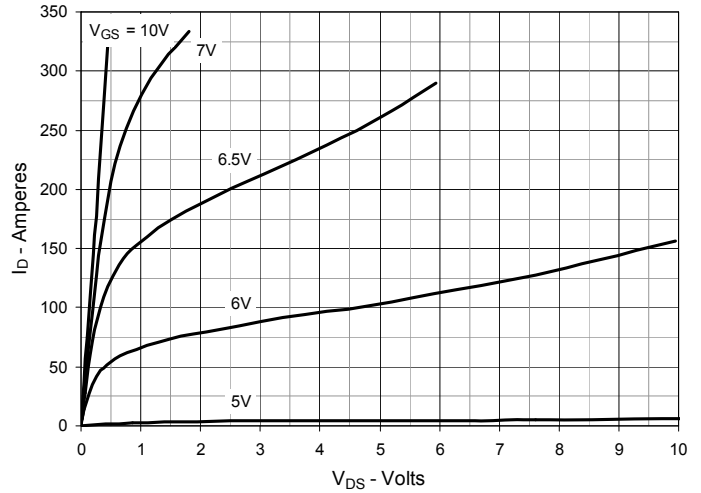


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

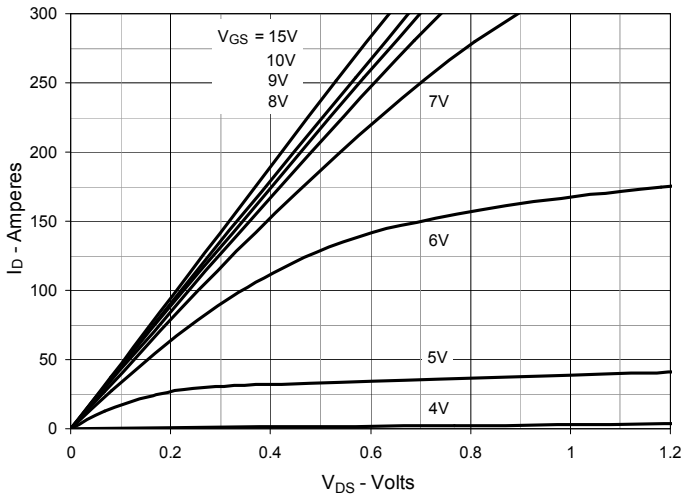


Fig. 4. Normalized $R_{DS(on)}$ to $I_D = 170\text{A}$ Value vs. Junction Temperature

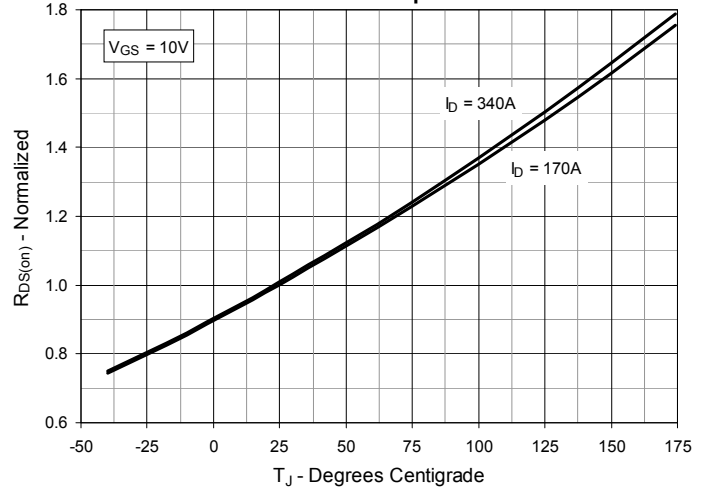


Fig. 5. Normalized $R_{DS(on)}$ to $I_D = 170\text{A}$ vs. Drain Current

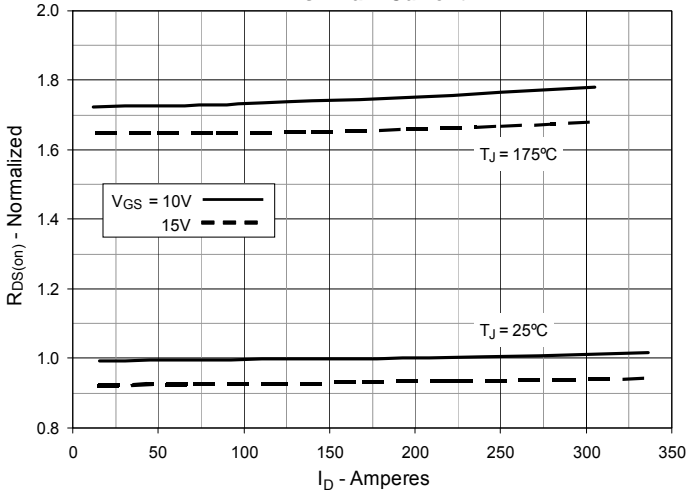


Fig. 6. Drain Current vs. Case Temperature

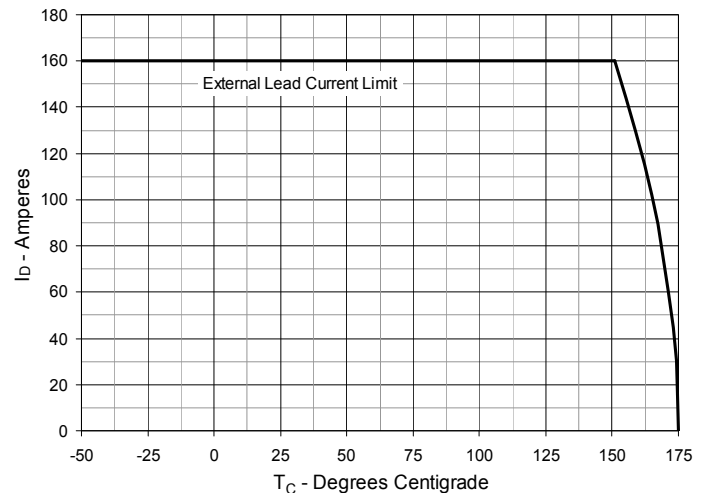


Fig. 7. Input Admittance

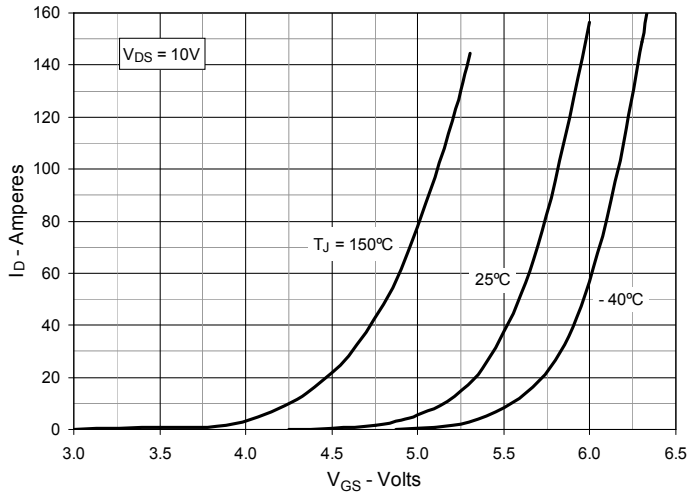


Fig. 8. Transconductance

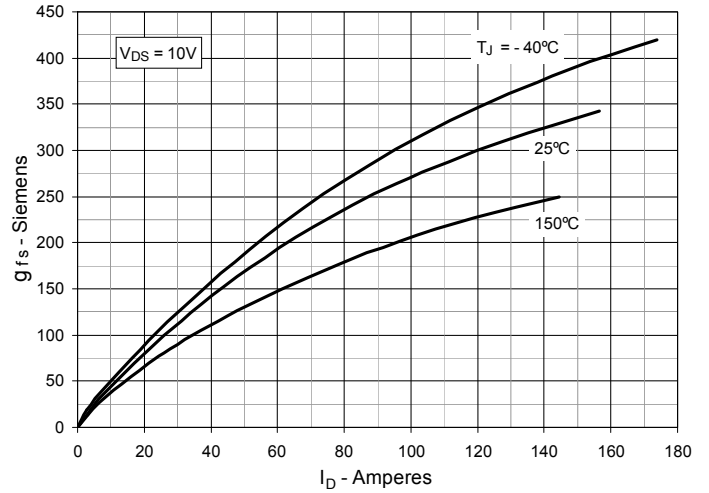


Fig. 9. Forward Voltage Drop of Intrinsic Diode

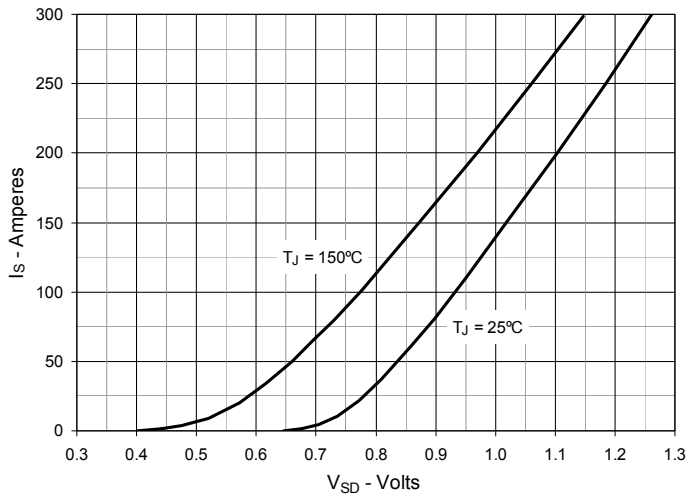


Fig. 10. Gate Charge

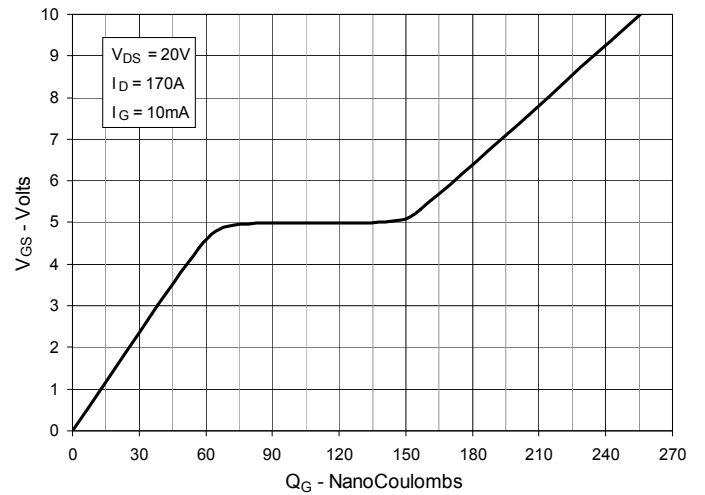


Fig. 11. Capacitance

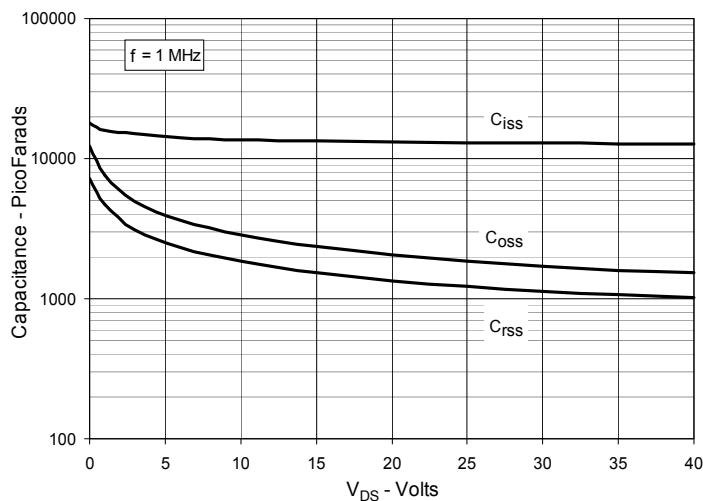


Fig. 12. Forward-Bias Safe Operating Area

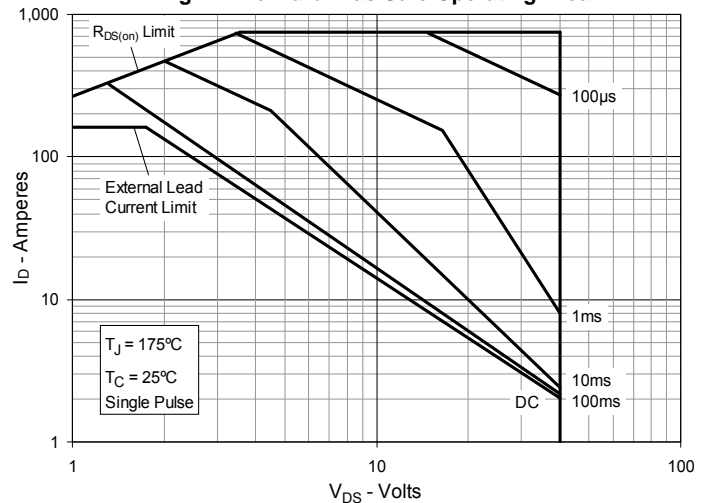


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

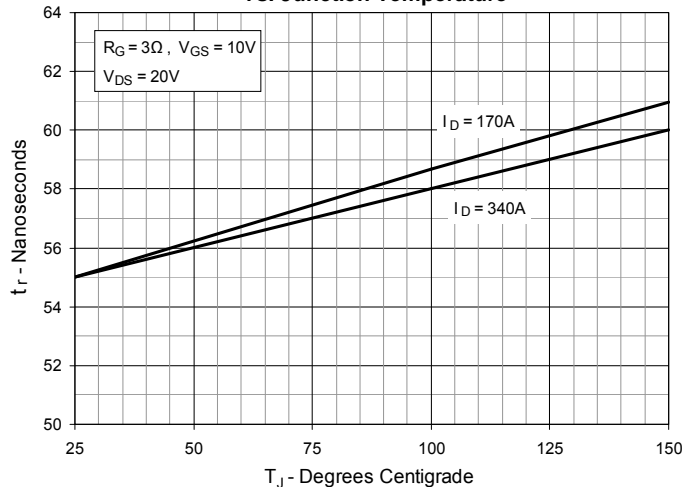


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

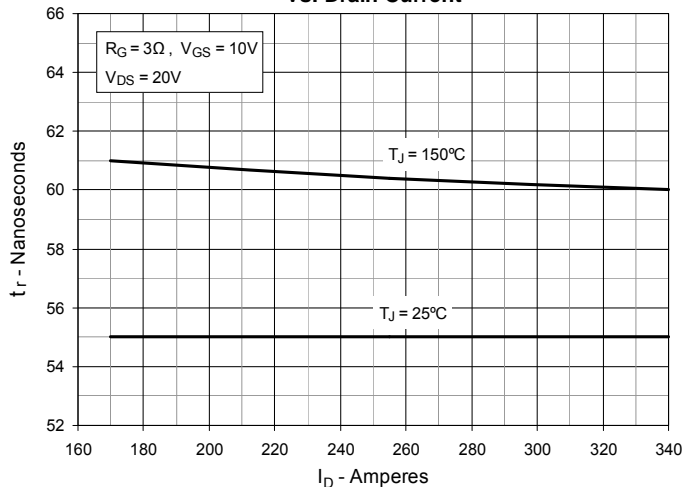


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

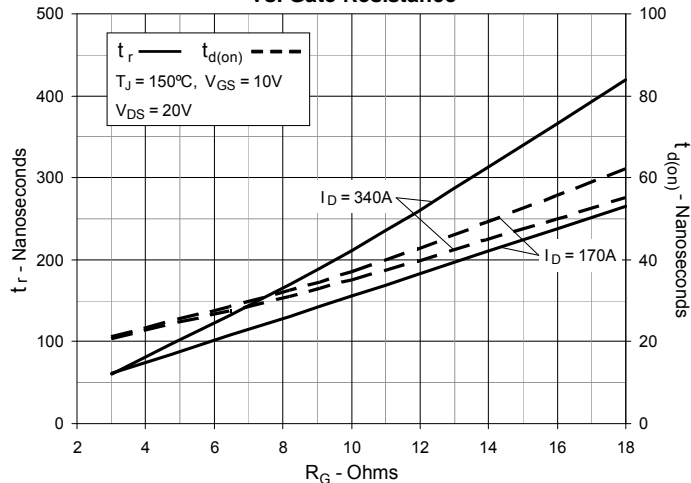


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

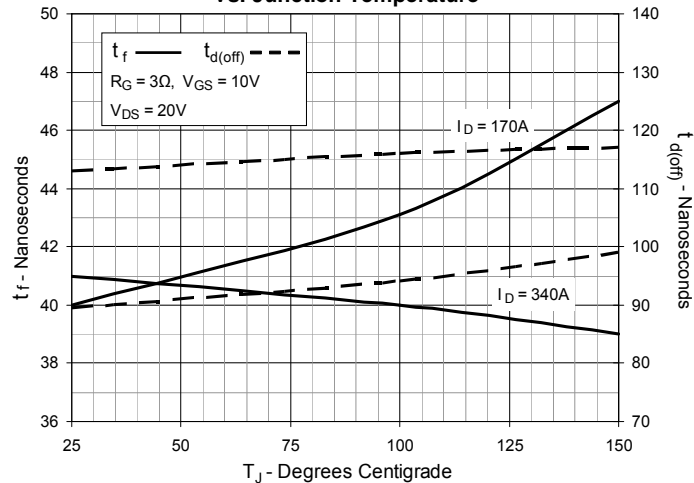


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

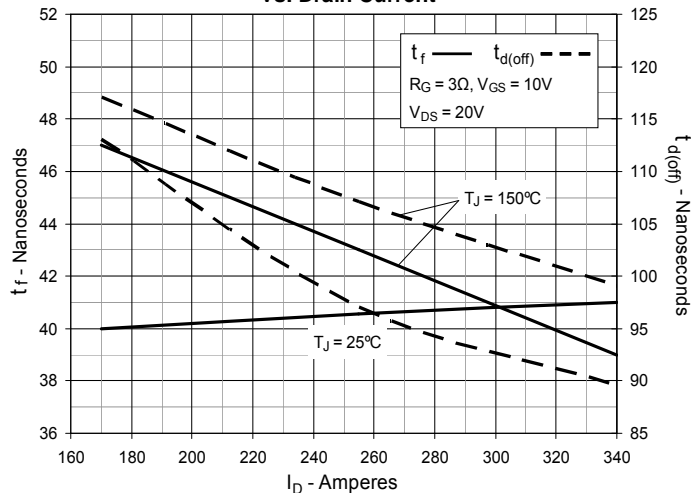


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

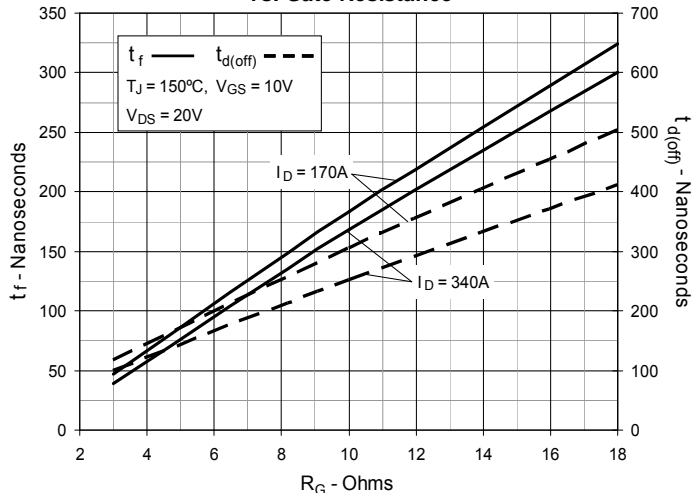
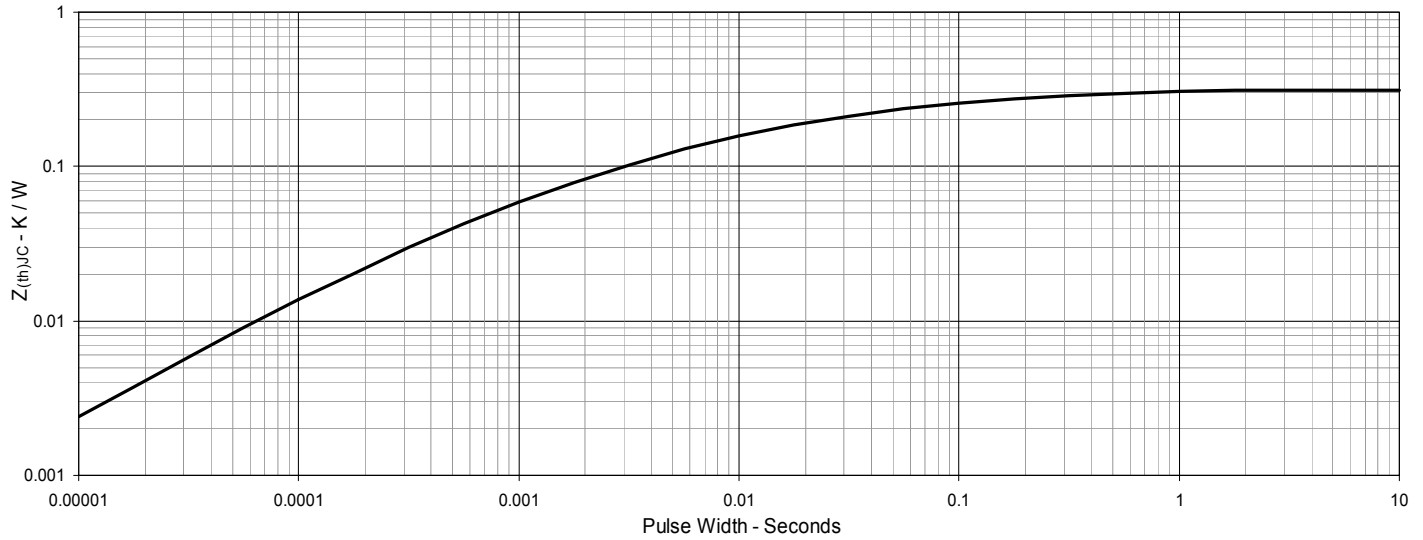
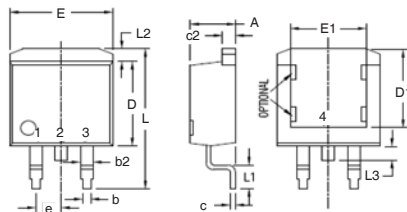


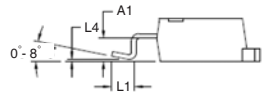
Fig. 19. Maximum Transient Thermal Impedance



TO-263 (IXTA) Outline

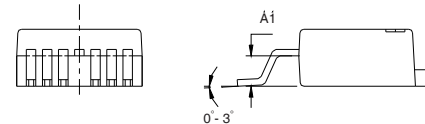
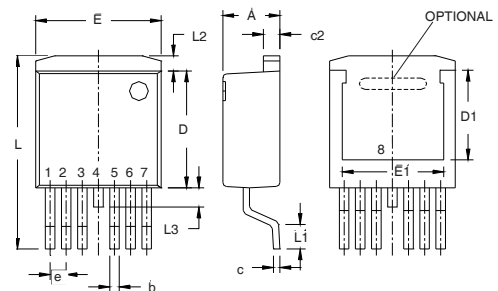


1 = Gate
2,4 = Drain
3 = Source



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-263 (7-lead) (IXTA..7) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50